



# NTMFS08N003C

## N-Channel Shielded Gate PowerTrench® MOSFET 80 V, 147 A, 3.1 mΩ

### Features

- Shielded Gate MOSFET Technology
- Max  $r_{DS(on)}$  = 3.1 mΩ at  $V_{GS} = 10$  V,  $I_D = 56$  A
- Max  $r_{DS(on)}$  = 8.1 mΩ at  $V_{GS} = 6$  V,  $I_D = 28$  A
- 50% lower  $Q_{rr}$  than other MOSFET suppliers
- Lowers switching noise/EMI
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

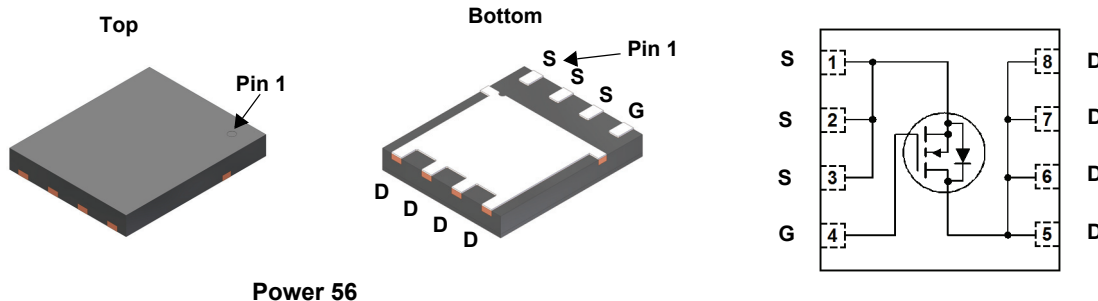


### General Description

This N-Channel MV MOSFET is produced using ON Semiconductor's advanced PowerTrench® process that incorporates Shielded Gate technology. This process has been optimized to minimise on-state resistance and yet maintain superior switching performance with best in class soft body diode.

### Applications

- Primary DC-DC MOSFET
- Synchronous Rectifier in DC-DC and AC-DC
- Motor Drive
- Solar



Power 56

### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
$V_{DS}$	Drain to Source Voltage	80	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous	$T_C = 25^\circ\text{C}$ (Note 5)	147
	-Continuous	$T_C = 100^\circ\text{C}$ (Note 5)	92
	-Continuous	$T_A = 25^\circ\text{C}$ (Note 1a)	22
	-Pulsed	(Note 4)	658
$E_{AS}$	Single Pulse Avalanche Energy	(Note 3)	486
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	125
	Power Dissipation	$T_A = 25^\circ\text{C}$ (Note 1a)	2.7
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	45	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
NTMFS08N003C	NTMFS08N003C	Power 56	13"	12 mm	3000 units

## Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}, V_{GS} = 0\text{ V}$	80			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		60		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 64\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA

### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 310\text{ }\mu\text{A}$	2.0	2.9	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 310\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		-8.2		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 56\text{ A}$		2.6	3.1	m $\Omega$
		$V_{GS} = 6\text{ V}, I_D = 28\text{ A}$		3.8	8.1	
		$V_{GS} = 10\text{ V}, I_D = 56\text{ A}, T_J = 125\text{ }^\circ\text{C}$		4.3	5.2	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 56\text{ A}$		123		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$		3820	5350	pF
$C_{oss}$	Output Capacitance			1335	1870	pF
$C_{rss}$	Reverse Transfer Capacitance			44	80	pF
$R_g$	Gate Resistance		0.1	0.6	1.3	$\Omega$

### Switching Characteristics

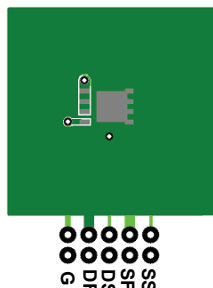
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 40\text{ V}, I_D = 56\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$		20	36	ns
$t_r$	Rise Time			8	16	ns
$t_{d(off)}$	Turn-Off Delay Time			40	64	ns
$t_f$	Fall Time			12	23	ns
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V to }10\text{ V}$	$V_{DD} = 40\text{ V},$ $I_D = 56\text{ A}$	52	73	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V to }6\text{ V}$		33	46	nC
$Q_{gs}$	Gate to Source Charge			17		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			10		nC
$Q_{oss}$	Output Charge	$V_{DD} = 40\text{ V}, V_{GS} = 0\text{ V}$		77		nC
$Q_{sync}$	Total Gate Charge Sync	$V_{DS} = 0\text{ V}, I_D = 56\text{ A}$		44		nC

### Drain-Source Diode Characteristics

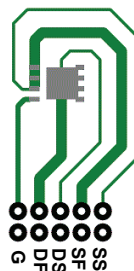
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2.2\text{ A}$ (Note 2)		0.7	1.2	V
		$V_{GS} = 0\text{ V}, I_S = 56\text{ A}$ (Note 2)		0.8	1.3	
$t_{rr}$	Reverse Recovery Time	$I_F = 28\text{ A}, di/dt = 300\text{ A}/\mu\text{s}$		28	45	ns
$Q_{rr}$	Reverse Recovery Charge			53	84	nC
$t_{rr}$	Reverse Recovery Time	$I_F = 28\text{ A}, di/dt = 1000\text{ A}/\mu\text{s}$		23	36	ns
$Q_{rr}$	Reverse Recovery Charge			121	194	nC

Notes:

1.  $R_{\theta JA}$  is determined with the device mounted on a  $1\text{ in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5\text{ in.}$  board of FR-4 material.  $R_{\theta CA}$  is determined by the user's board design.



a.  $45\text{ }^\circ\text{C/W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper.



b.  $115\text{ }^\circ\text{C/W}$  when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width <  $300\text{ }\mu\text{s}$ , Duty cycle < 2.0%.

3.  $E_{AS}$  of 486 mJ is based on starting  $T_J = 25\text{ }^\circ\text{C}$ ; N-ch:  $L = 3\text{ mH}, I_{AS} = 18\text{ A}, V_{DD} = 80\text{ V}, V_{GS} = 10\text{ V}$ . 100% test at  $L = 0.1\text{ mH}, I_{AS} = 57\text{ A}$ .

4. Pulsed  $I_D$  please refer to Fig 11 SOA graph for more details.

5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted.

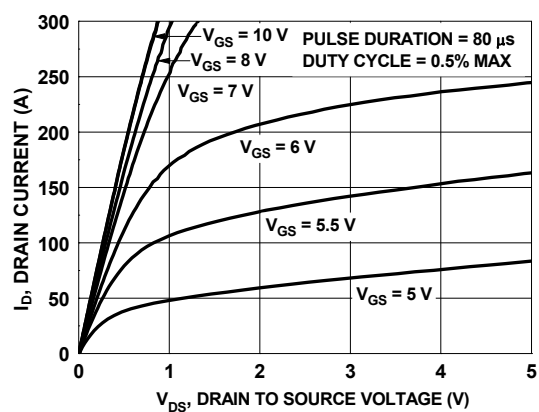


Figure 1. On Region Characteristics

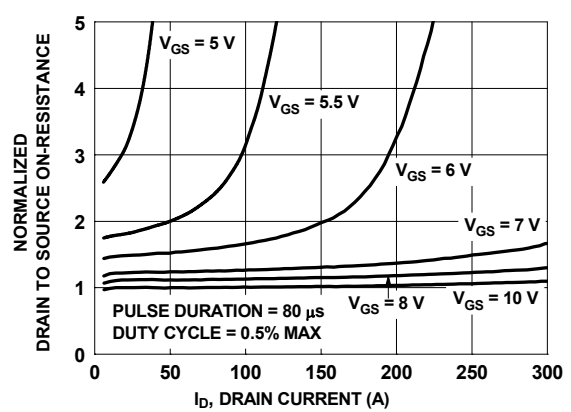


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

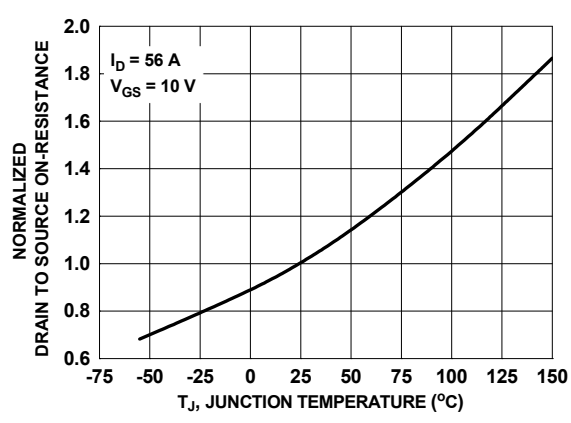


Figure 3. Normalized On Resistance vs. Junction Temperature

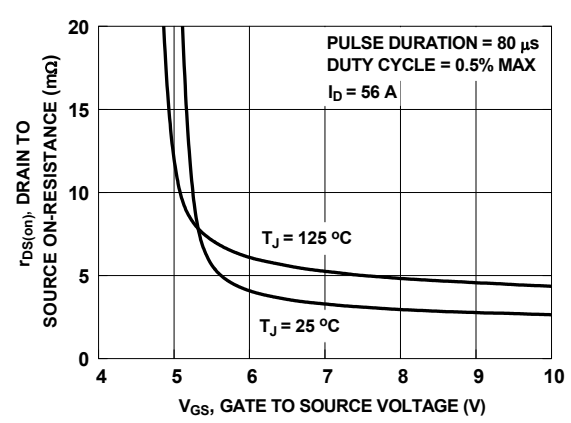


Figure 4. On-Resistance vs. Gate to Source Voltage

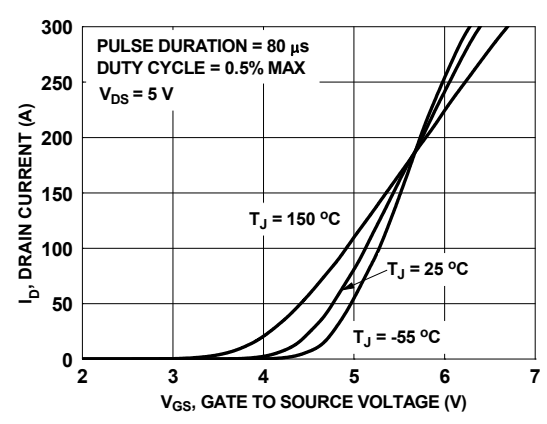


Figure 5. Transfer Characteristics

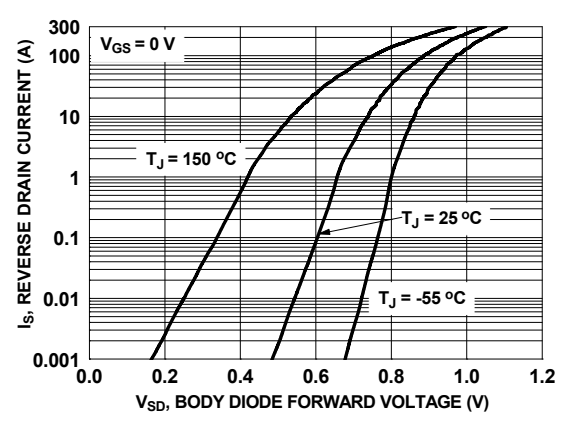
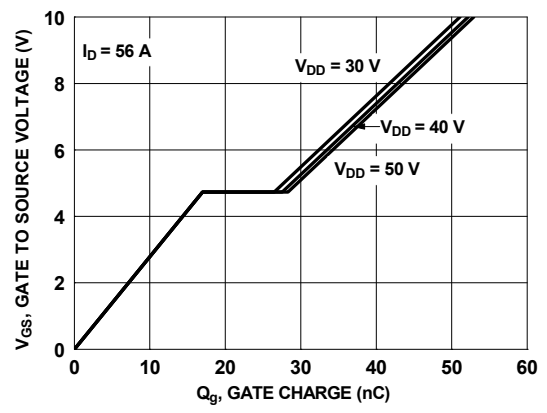
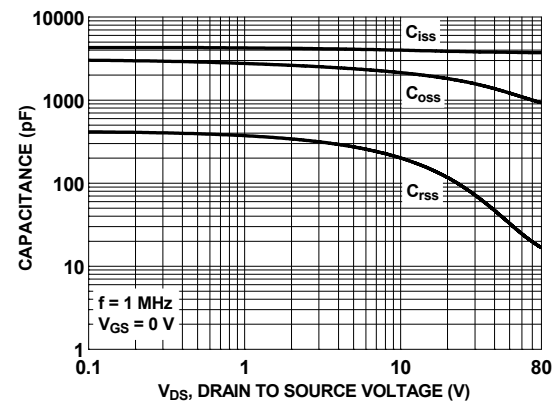


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

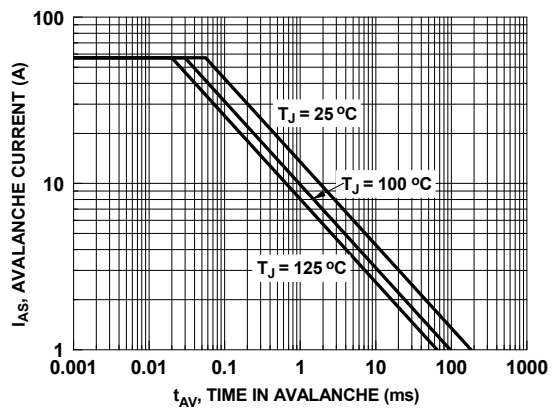
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted.



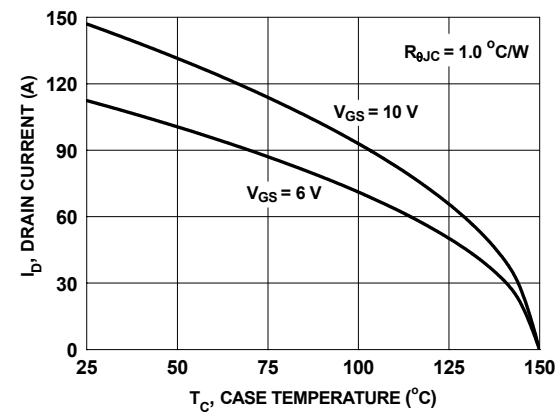
**Figure 7. Gate Charge Characteristics**



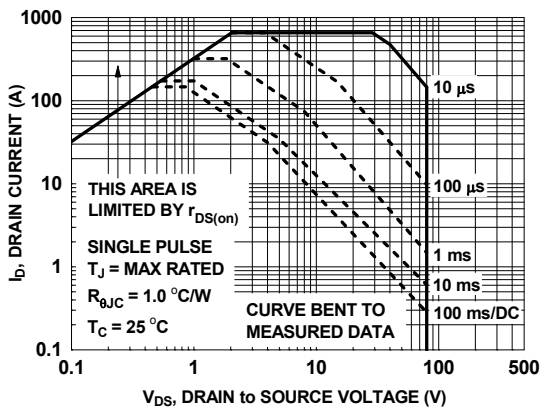
**Figure 8. Capacitance vs. Drain to Source Voltage**



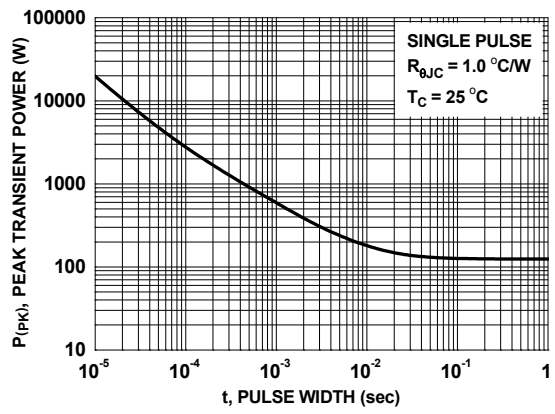
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs. Case Temperature**

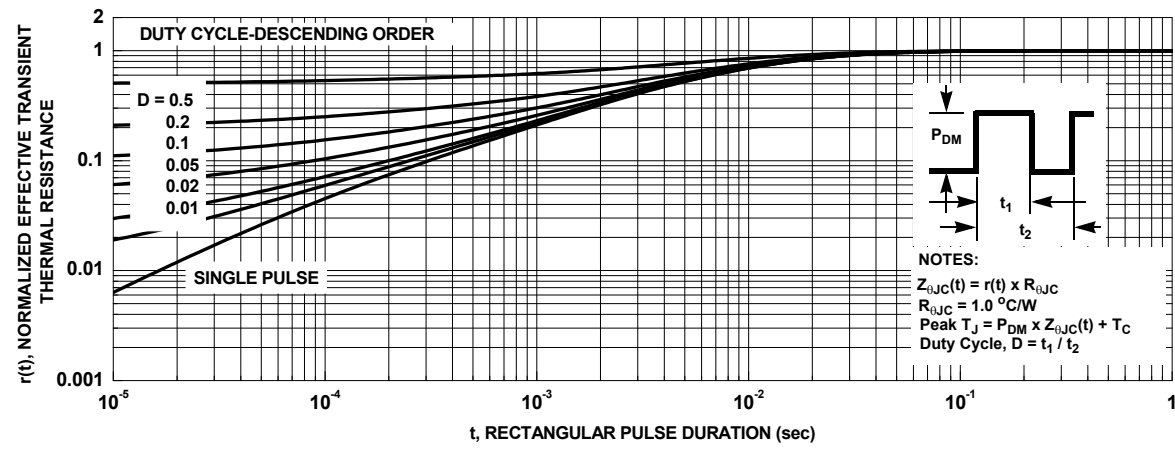


**Figure 11. Forward Bias Safe Operating Area**



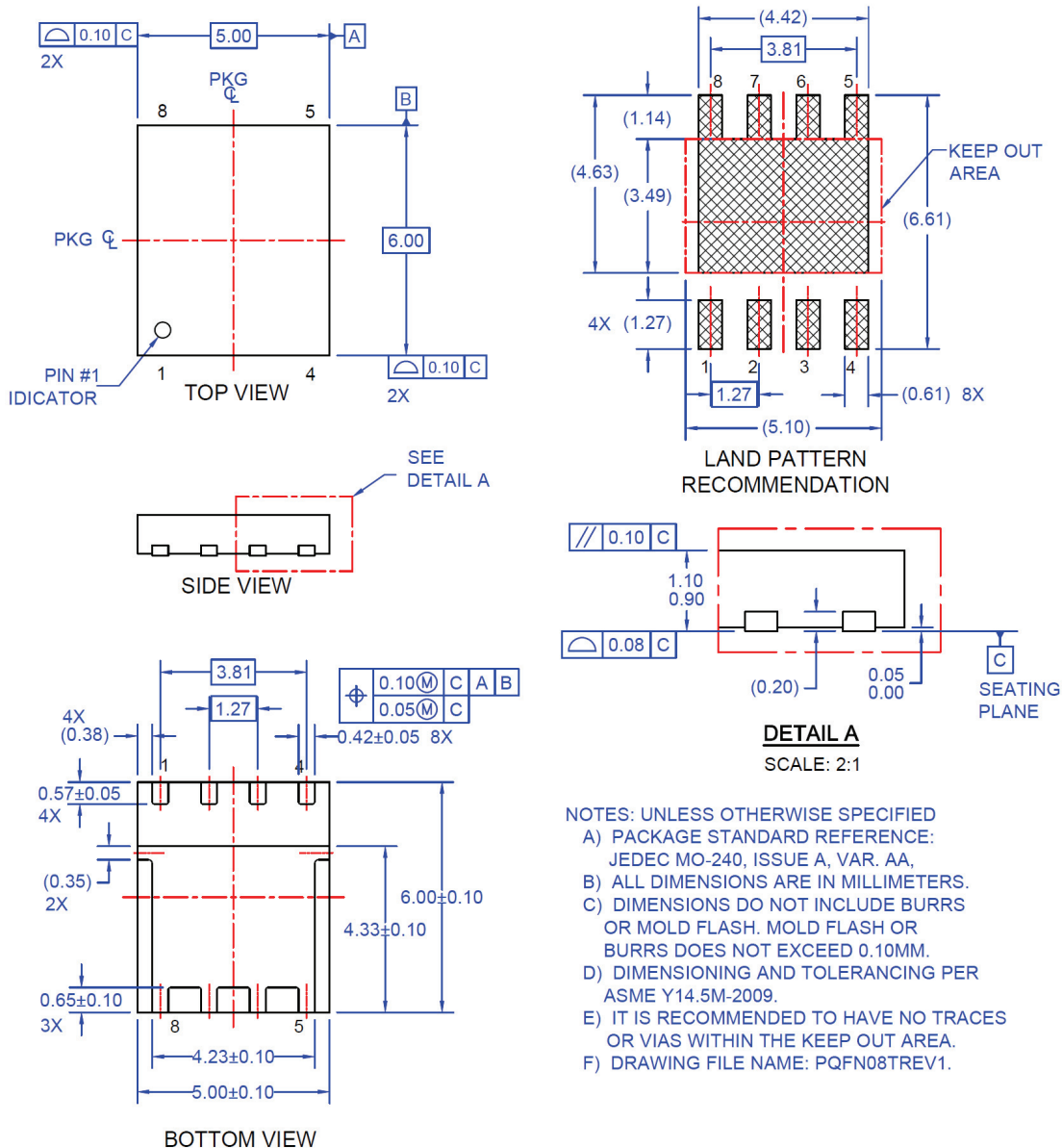
**Figure 12. Single Pulse Maximum Power Dissipation**

**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted.



**Figure 13. Junction-to-Case Transient Thermal Response Curve**

## Dimensional Outline and Pad Layout



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